

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [75] with the following amended paragraph:

[75] Wall charges occurred upon the plasma discharge is accumulated on the upper dielectric layer 114. The protection film 116 serves to prevent damage of the upper dielectric layer 114 due to sputtering generated upon the plasma discharge and to increase emission efficiency of secondary electrons. The protection film 116 is usually formed using magnesium oxide (MgO). A lower dielectric layer 122 and a diaphragm 124 are formed on a lower substrate ~~447~~118 in which the address electrode X is formed. A fluorescent material layer 126 is covered on the lower dielectric layer 122 and the diaphragm 124. In the above, the address electrode X are formed in the direction intersecting the scan electrode Y and the sustain electrode Z.